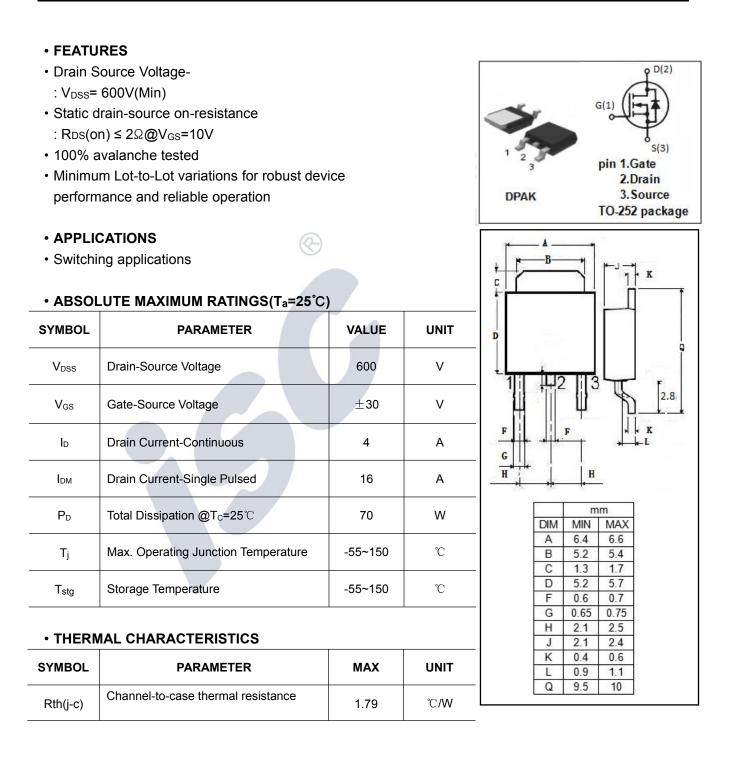


INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

STD4NK60ZT4





isc N-Channel MOSFET Transistor

STD4NK60ZT4

ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =1mA	600			V
V _{GS} (th)	Gate Threshold Voltage	VDS=VGS; I _D =50	3		4.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =2A			2	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V			±10	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V V _{DS} =600V; V _{GS} = 0V;TC=125°C			1 50	μA
V _{SD}	Diode forward voltage	Isd= 4A, V _{GS} = 0V			1.6	V

NOTICE:

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